Part Number	Customer

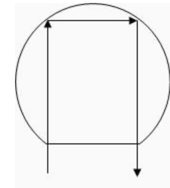
Category		Parameter	Specification	Measurement Method
OverallWafer	1.0	Diameter	100.00 +/- 0.50 mm	Wafer Vendor
	2.0	Primary Flat Orientation	{110}+/-0.5 degree	Wafer Vendor
	3.0	Primary Flat Length	32.50 +/- 2.50 mm	Wafer Vendor
	4.0	Secondary Flat Orientation	none/semi std	
	5.0	Overall Thickness	463.00 +/- 6.00 µm	ADE, 100%
	6.0	Total Thickness Variation (TTV)	<3.00µm	Guaranteed by Process
	6.5	Global Flatness (TIR)	<3.00um	ADEmeasurement 100%
	7.0	Bow	<50.00µm	ADE to ASTM F534, 20%
	8.0	Warp	<50.00µm	ADE to ASTM F657, 20%
	9.0	Edge Chips	0	Bright Light, 100% (note 2)
	10.0	Edge Exclusion	5mm	
HandleSilicon	11.0	Handle Growth Method	CZ	Wafer Vendor
	12.0	Handle Orientation	{100} +/- 1 degree	Wafer Vendor
	13.0	Handle Doping Type	N	Wafer Vendor
	14.0	Handle Dopant	Phosphorous	Wafer Vendor
	15.0	Handle Resistivity	5 - 10 Ohmcm	Wafer Vendor
	16.0	Handle Thickness	450.00 +/- 5.00 um	ADE, 100%inspection
	16.1	Backside Finish	lapped	Guaranteed by Process
BuriedOxide	17.0	Oxide Thickness	10,000.00 +/- 500.00 A	
DeviceSilicon	25.4	Device Growth Method	CZ	Wafer Vendor
	26.0	Device Orientation	{100} +/- 0.5 degree	Wafer Vendor
	27.0	Device Doping Type	N	Wafer Vendor
	28.0	Device Dopant	Phosphorous	Wafer Vendor
	29.0	Device Resistivity	1 - 3 Ohmcm	Wafer Vendor
	29.5	Nominal Thickness	12.50 +/- 0.50 um	FTIR 9 point measurement (see note 1)
	29.6	Distance to device silicon edge from wafer edge	<2mm	Guaranteed by process
	30.0	Surface	roughness < 3A rms	Guaranteed by process
	31.0	Voids	none inside 5mm edge exclusion	Bright Light inspection 100%
	32.0	Scratches	none	Bright Light inspection 100%
	33.0	Haze	none	Bright Light inspection

Part Number	Customer

Category	Parameter	Specification	Measurement Method
Shipping Details	Wafer per box :	Max 25	
	Packaging :	Taped Polypropylene Wafer Box Empak, Ultrapak, 100.00mm Antistatic Double Bagging	
	Lot Shipment Data	Device Thickness Bow / Warp Data Handle and SOI Thickness	

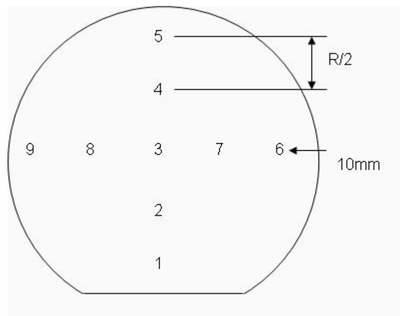
Explanatory Notes

1. Microscope inspection performed using microscope scan as below. 5x objective.



2. All bright light inspections performed exclude all wafer area outside the edge exclusion defined in Overall Wafer, Edge Exclusion. High intensity bright lamp inspection as per ASTM F523.

3. 9 point measurement are as shown in the diagram below:



Additional Information